

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

NAKAMURA et al

Atty. Ref.: 160-399; Confirmation No.

Appl. No. To be Assigned

Group:

Filed: November 24, 2003

Examiner:

For: NITRIDE SEMICONDUCTOR WITH ACTIVE LAYER OF QUANTUM WELL
STRUCTURE WITH INDIUM-CONTAINING NITRIDE SEMICONDUCTOR

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November 24, 2003

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

PRELIMINARY AMENDMENT

In order to place the above-identified application in better condition for
examination, please amend the application as follows:

IN THE TITLE

Amend the title so that it reads as follows:

NITRIDE SEMICONDUCTOR ~~DEVICE~~ WITH ACTIVE LAYER OF
QUANTUM WELL STRUCTURE WITH INDIUM-CONTAINING NITRIDE
SEMICONDUCTOR